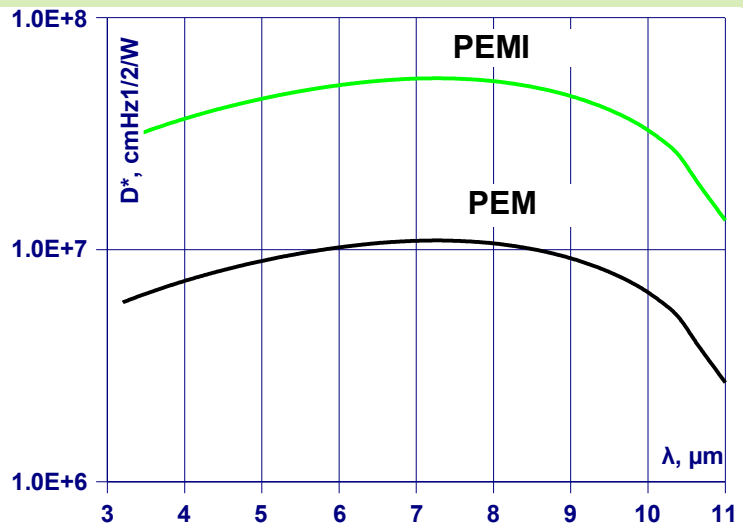


PEM- and PEMI-Series

10.6 μm PHOTOELECTROMAGNETIC IR DETECTORS AMBIENT TEMPERATURE OPTICALLY IMMERSED or not



FEATURES

- Ambient temperature operation
- No bias required
- Wide spectral range (2-12 μm)
- $D^*(10.6 \mu\text{m})$ up to $2 \cdot 10^7 \text{ cmHz}^{1/2}/\text{W}$
- Response time of 1 ns or less
- No flicker (1/f) noise
- Operation from DC to HF
- Lightweight, rugged and reliable
- Convenient to use
- Low cost
- Custom design upon request

DESCRIPTION

The PEM- and PEMI-series detectors are photovoltaic and operate on the photoelectromagnetic effect. The devices are typically optimized for the best performance at 10.6 μm . PEMI-types are optically immersed on high refractive index GaAs hyperhemispherical (standard) or hemispherical (optional) lenses. The detector include an advanced semiconductor (Hg,Cd)Te with controlled composition and doping profiles, and miniature permanent magnets to produce very strong magnetic fields.

PEM and PEMI detectors are exceptionally well suited for heterodyne detection of 10.6 μm radiation. Exhibiting no flicker (1/f) noise, and they can be used simultaneously for detection of CW and low frequency modulated radiation in the whole 2-12 μm spectral range. Custom detectors such as quadrant cells and multielement arrays, various specialized packages and connectors are available upon request.

SPECIFICATION*

@ 20°C

CHARACTERISTICS	UNITS	PEM-10.6	PEMI-10.6
λ_{op}	μm	10.6	10.6
Detectivity: at λ_{peak} at λ_{op}	$\text{cmHz}^{1/2}/\text{W}$	$\geq 1.5 \times 10^7$ $\geq 4 \times 10^6$	$\geq 8 \times 10^7$ $\geq 2 \times 10^7$
Responsivity	V/W	≥ 0.04	≥ 0.2
Response time	ns	≤ 1	≤ 1
Resistance	Ω	40 to 100	40 to 100
Optical area length*width	mm*mm	0.1*0.1; 0.25*0.25; 0.5*0.5; 1*1; 2*2	
Operating temperature	K	300	
Field of view, F/#	deg	60, 0.5	38, 1.65

* Data sheet states minimum D^* values for each detector model. Higher performance detectors can be provided upon request. See application notes for more details.



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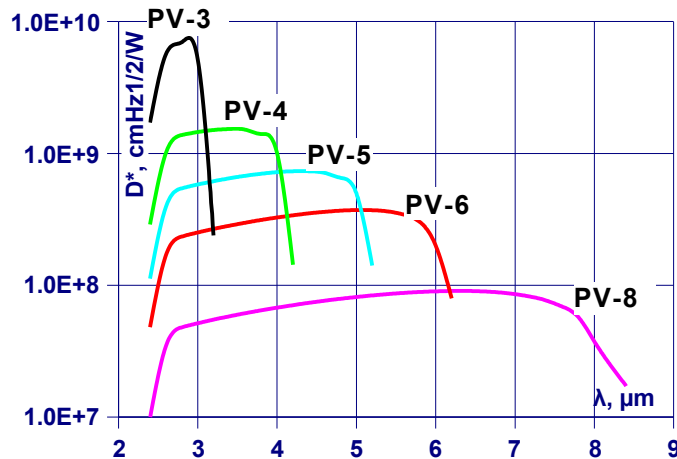
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PV-Series

2-11 μm IR PHOTOVOLTAIC DETECTORS



FEATURES

- Ambient temperature operation
- No bias required
- Short response time
- No flicker (1/f) noise
- Operation from DC to VHF
- Perfect match to fast electronics
- Wide dynamic range
- Low cost
- Custom design upon request

DESCRIPTION

The PV-n series photodetectors (where n is wavelength λ_{op} in micrometers at which the detector is optimized) are IR photovoltaic detectors. These devices can be optimized for the maximum performance anywhere within 2.5 to 11 μm range. High performance and stability were achieved by using variable bandgap (Hg,Cd)Te semiconductor, optimized doping and improved surface processing. Custom devices with quadrant cells, multielement arrays, various immersion lenses, windows and optical filters are available on request. Standard detectors are available in modified TO-39 or BNC-based packages with no windows. Other packages, windows and connectors are available upon request. See application notes for more details. Multiple cells connected in series are preferable for large area devices. They are characterized by similar D^* , larger parallel resistance and lower R_i . See our PVM-series.

SPECIFICATION*

@ 20°C

CHARACTERISTICS	UNITS	PV-3	PV-4	PV-5	PV-6	PV-8
λ_{op}	μm	3	4	5	6	8
Detectivity: at λ_{peak} at λ_{op}	$\text{cmHz}^{1/2}/\text{W}$	$\geq 8 \times 10^9$ $\geq 5 \times 10^9$	$\geq 1.5 \times 10^9$ $\geq 1 \times 10^9$	$\geq 8 \times 10^8$ $\geq 5 \times 10^8$	$\geq 4 \times 10^8$ $\geq 2 \times 10^8$	$\geq 8 \times 10^7$ $\geq 4 \times 10^7$
Responsivity	A/W	≥ 1.2	≥ 1.2	≥ 1.2	≥ 1	≥ 0.5
Response time	ns	$\leq 15^{**}$	$\leq 15^{**}$	$\leq 15^{**}$	$\leq 12^{**}$	$\leq 7^{**}$
Parallel resistance-optical area product	$\Omega \times \text{cm}^2$	≥ 0.05	≥ 0.01	≥ 0.003	≥ 0.001	≥ 0.0002
Optical area length \times width or diameter for round devices	mm \times mm	0.025 \times 0.025; 0.05 \times 0.05; 0.1 \times 0.1; 0.25 \times 0.25; 0.5 \times 0.5; 1 \times 1; 2 \times 2; \varnothing 0.025; \varnothing 0.05; \varnothing 0.1; \varnothing 0.25; \varnothing 0.5; \varnothing 1; \varnothing 2; \varnothing 3				
Operating temperature	K	300				
Acceptance angle, F#	deg	60, 0.5				

* Data sheet states minimum D^* values for each detector model. Higher performance detectors can be provided upon request.

** Faster response may be achieved at reverse bias and with high-frequency-optimized devices.

See application notes for more details.



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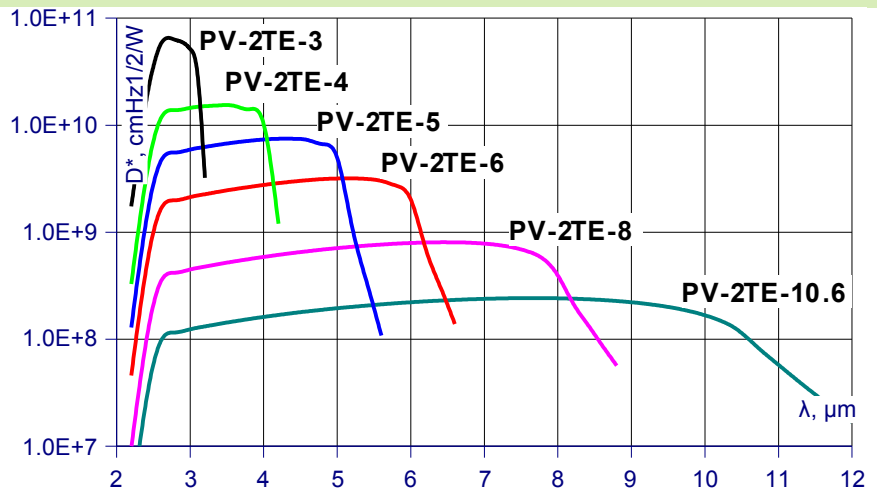
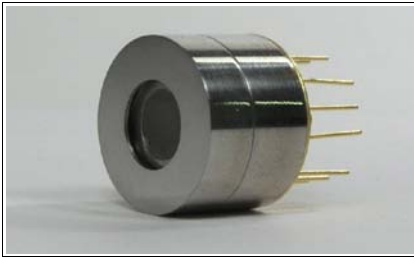
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AP, 15.12.05

SERIES PV-2TE

2-12 μm IR PHOTOVOLTAIC DETECTORS THERMOELECTRICALLY COOLED



● FEATURES

- High performance in the 2-12 μm range without LN-cooling!
- Fast response
- No flicker noise
- Convenient to use
- Wide dynamic range
- Compact, rugged and reliable
- Low cost
- Prompt delivery
- Custom design upon request

● DESCRIPTION

The PV-2TE-n series photodetectors (where n is wavelength λ_{op} , in micrometers, for which the detector is optimized) are two-stage TE-cooled IR photovoltaic detectors. These devices can be optimized for the maximum performance anywhere within 2.5 to 12 μm range. High performance and stability were achieved by using a variable bandgap (Hg,Cd)Te semiconductors, optimized doping and improved surface processing. Custom devices with quadrant cells, multielement arrays, various immersion lenses, windows and optical filters are available on request.

Standard detectors are available in modified TO-8 packages with BaF₂ windows. Other packages, windows and connectors are available upon request. See application notes for more details.

Multiple cells connected in series are preferable for large area devices. They are characterized by similar D*, larger parallel resistance and lower R_i. See our PVM-series for details.

SPECIFICATION*

@ 20°C

CHARACTERISTICS	UNITS	PV-2TE-3	PV-2TE-4	PV-2TE-5	PV-2TE-6	PV-2TE-8	PV-2TE-10.6	
λ_{op}	μm	3	4	5	6	8	10.6	
Detectivity:								
at λ_{peak}	cmHz ^{1/2} /W	≥8x10 ¹⁰	≥1.5x10 ¹⁰	≥8x10 ⁹	≥4x10 ⁹	≥8x10 ⁹	≥3x10 ⁸	
at λ_{op}	W	≥5x10 ¹⁰	≥1E x10 ¹⁰	≥5x10 ⁹	≥2x10 ⁹	≥4x10 ⁹	≥1x10 ⁸	
Responsivity	A/W	≥1.2	≥1.3	≥1.3	≥1.2	≥1	≥0.7	
Response time	ns	≤15**	≤20**	≤20**	≤10**	≤7**	≤3**	
Parallel resistance-optical area product	Ω×cm ²	≥0.3	≥0.10	≥0.02	≥0.006	≥0.001	≥0.0001	
Optical area length × width or diameter for round devices	mm×mm mm	0.025×0.025; 0.05×0.05; 0.1×0.1; 0.25×0.25; 0.5×0.5; 1×1; 2×2; ø0.025; ø0.05; ø0.1; ø0.25; ø0.5; ø1; ø2; ø3					See PVM-2TE for large areas	
Operating temperature	K	220 to 240						
Acceptance angle, F#	deg	60, 0.5						

* Data sheet states minimum D* values for each detector model. Higher performance detectors can be provided upon request.

** Faster response may be achieved at reverse bias and with high-frequency-optimized devices. See application notes for more details.



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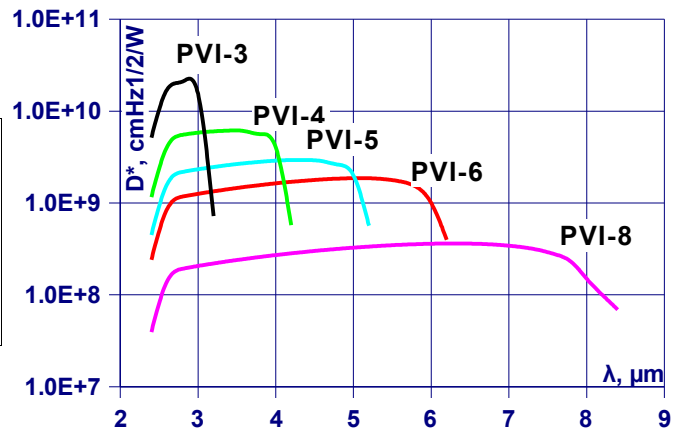
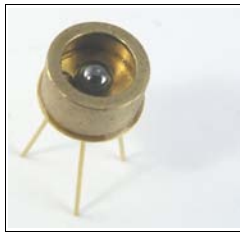
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AP, 15.12.05



FEATURES

- Ambient temperature operation
- No bias required
- Short response time
- No flicker (1/f) noise
- Operation from DC to VHF
- Perfect match to fast electronics
- Wide dynamic range
- Low cost
- Custom design upon request

DESCRIPTION

The PVI-n series photodetectors (where n is wavelength λ_{op} in micrometers at which the detector is optimized) are IR photovoltaic detectors which have been optically immersed on high refractive index GaAs hyperhemispherical (standard) or hemispherical (optional) lenses. These devices can be optimized for the maximum performance anywhere within 2.5 to 11 μm range. High performance and stability are achieved by using a variable gap (Hg,Cd)Te semiconductors, optimized doping and improved surface processing. Custom devices with quadrant cells, multielement arrays, various immersion lenses, windows and optical filters are available on request. Standard detectors are available in modified TO-39 or BNC-based packages with no windows. Other packages, windows and connectors are available upon request. See application notes for more details. Multiple cells connected in series are preferable for large area devices. They are characterized by similar D^* , larger parallel resistance and lower R_i .

SPECIFICATION*

@ 20°C

CHARACTERISTICS	UNITS	PVI-3	PVI-4	PVI-5	PVI-6	PVI-8
λ_{op}	μm	3	4	5	6	8
Detectivity:						
at λ_{peak}	$\text{cmHz}^{1/2}/\text{W}$	$\geq 2 \times 10^{10}$	$\geq 6 \times 10^9$	$\geq 3 \times 10^9$	$\geq 2 \times 10^9$	$\geq 3 \times 10^8$
at λ_{op}		$\geq 1.5 \times 10^{10}$	$\geq 4 \times 10^9$	$\geq 2 \times 10^9$	$\geq 1 \times 10^9$	$\geq 1.5 \times 10^8$
Responsivity	A/W	≥ 1.2	≥ 1.3	≥ 1.3	≥ 1.2	≥ 1
Response time	ns	$\leq 15^{**}$	$\leq 15^{**}$	$\leq 15^{**}$	$\leq 12^{**}$	$\leq 7^{**}$
Parallel resistance-optical area product	$\Omega \times \text{cm}^2$	≥ 5	≥ 1	≥ 0.3	≥ 0.1	≥ 0.02
Optical area length \times width or diameter for round devices	mm \times mm mm	0.2 \times 0.2; 0.25 \times 0.25; 0.5 \times 0.5; 1 \times 1; 2 \times 2; \emptyset 0.2; \emptyset 0.25; \emptyset 0.5; \emptyset 1; \emptyset 2; \emptyset 3				
Operating temperature	K	300				
Acceptance angle, F#	deg	35, 1.65				

* Data sheet states minimum D^* values for each detector model. Higher performance detectors can be provided upon request.
 ** Faster response may be achieved at reverse bias and with high-frequency-optimized devices.
 See application notes for more details.



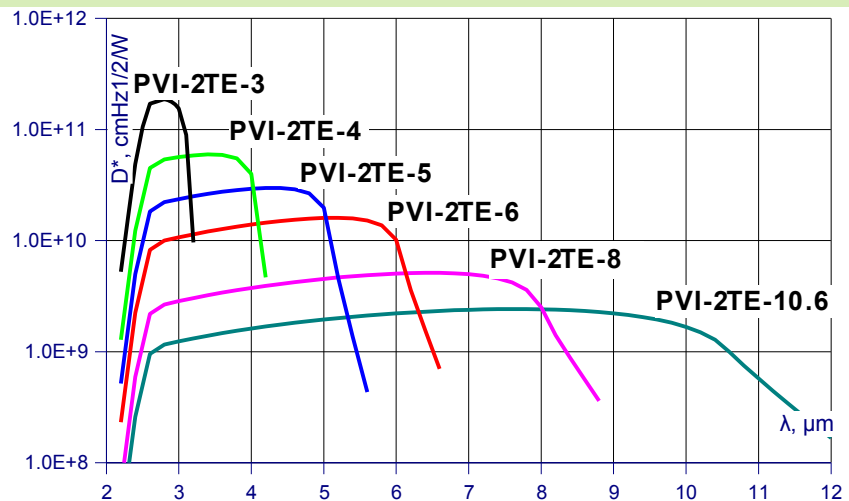
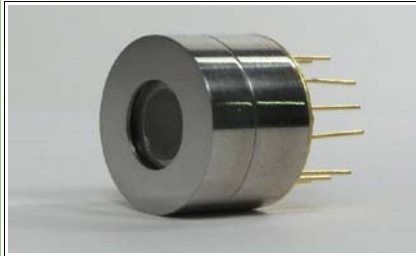
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PVI-2TE Series

2-12 μm IR PHOTOVOLTAIC DETECTORS THERMOELECTRICALLY COOLED OPTICALLY IMMERSED



FEATURES

- High performance in the 2-12 μm range without LN-cooling!
- Fast response
- No flicker (1/f) noise
- Convenient to use
- Wide dynamic range
- Compact, rugged and reliable
- Low cost
- Prompt delivery
- Custom design upon request

DESCRIPTION

The PVI-2TE-n series photodetectors (where n is wavelength λ_{op} , in micrometers, for which the detector is optimized) are two-stage TE-cooled IR photovoltaic detectors which are optically immersed on high refractive index GaAs hyperhemispherical (standard) or hemispherical (optional) lenses. These devices can be optimized for maximum performance anywhere within the 2.5 to 11 μm range. High performance and stability are achieved by using improved variable bandgap (Hg,Cd)Te semiconductors, optimized doping and improved surface processing. Custom devices are available on request. Standard detectors are available in modified TO-8 packages with BaF₂ windows. Other packages, windows and connectors are available upon request. See application notes for more details. Multiple cells connected in series are preferable for devices with larger area. They are characterized by similar D*, larger parallel resistance and lower R_i. See our PVM- and PVMI-series devices for these.

SPECIFICATION*

@ 20°C

CHARACTERISTICS	UNITS	PVI-2TE-3	PVI-2TE-4	PVI-2TE-5	PVI-2TE-6	PVI-2TE-8	PVI-2TE-10.6	
λ_{op}	μm	3	4	5	6	8	10.6	
Detectivity:								
at λ_{peak}	$\text{cmHz}^{1/2}/\text{W}$	$\geq 2 \times 10^{11}$	$\geq 6 \times 10^{10}$	$\geq 3 \times 10^{10}$	$\geq 2 \times 10^{10}$	$\geq 5 \times 10^9$	$\geq 3 \times 10^9$	
at λ_{op}		$\geq 1.5 \times 10^{11}$	$\geq 4 \times 10^{10}$	$\geq 2 \times 10^{10}$	$\geq 1 \times 10^{10}$	$\geq 2 \times 10^9$	$\geq 1 \times 10^9$	
Responsivity	A/W	≥ 1.2	≥ 1.3	≥ 1.3	≥ 1.2	≥ 1	≥ 0.7	
Response time	ns	$\leq 15^{**}$	$\leq 20^{**}$	$\leq 20^{**}$	$\leq 10^{**}$	$\leq 7^{**}$	$\leq 3^{**}$	
Parallel resistance-optical area product	$\Omega \times \text{cm}^2$	≥ 30	≥ 10	≥ 2	≥ 0.60	≥ 0.1	≥ 0.01	
Optical area length \times width or diameter for round devices	mm \times mm mm		0.2 \times 0.2; 0.25 \times 0.25; 0.5 \times 0.5; 1 \times 1; 2 \times 2; \emptyset 0.2; \emptyset 0.25; \emptyset 0.5; \emptyset 1; \emptyset 2; \emptyset 3				Up to 0.5 \times 0.5 - See PVMI-2TE-10.6 for larger areas	
Operating temperature	K	220 to 240						
Acceptance angle, F#	deg	35, 1.65						

* Data sheet states minimum D* values for each detector model. Higher performance detectors can be provided upon request.

** Faster response may be achieved at reverse bias and with high-frequency-optimized devices.

See application notes for more details.



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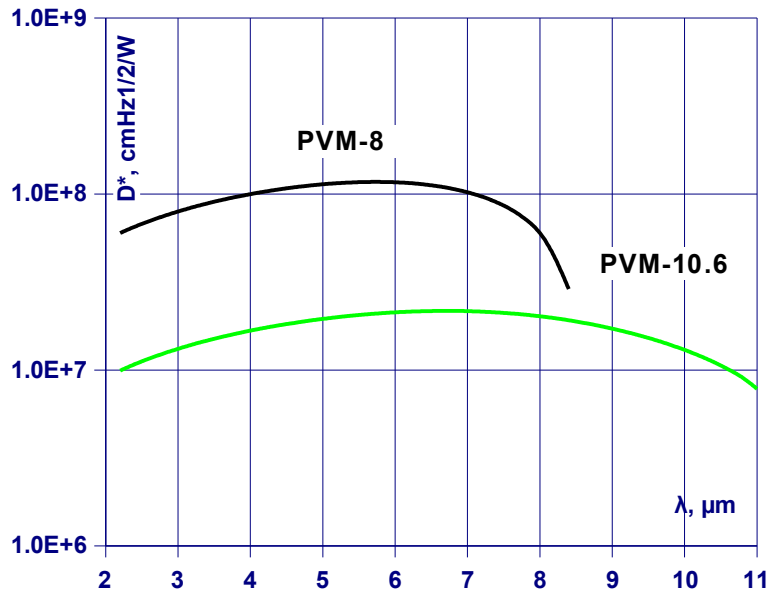
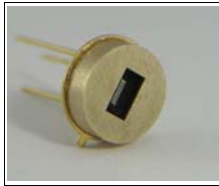
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SERIES PVM

8-12 μm IR PHOTOVOLTAIC MULTIPLE JUNCTION DETECTORS



FEATURES

- Ambient temperature operation
- No bias required
- Short response time
- No flicker (1/f) noise
- Operation from DC to VHF
- Perfect match to fast electronics
- Wide dynamic range
- Large area devices
- Low cost
- Custom design upon request

DESCRIPTION

The PVM-n series photodetectors (where n is wavelength λ_{op} in micrometers at which the detector is optimized) are multiple heterojunction photovoltaic IR detectors. These devices are especially useful as fast large area detectors operating within the 2 to 12 μm range. High performance and stability are achieved by using a variable gap (Hg,Cd)Te semiconductor, optimized doping and improved surface processing. Custom devices with quadrant cells, multielement arrays, various immersion lenses, windows and optical filters are available on request. Standard detectors are available in modified TO-39 or BNC-based packages with no windows. Other packages, windows and connectors are available upon request. See application notes for more details.

SPECIFICATION

@ 20°C

CHARACTERISTICS*	UNITS	PVM-8	PVM-10.6
λ_{op}	μm	8	10.6
Detectivity: at λ_{peak} at λ_{op}	$\text{cmHz}^{1/2}/\text{W}$	$\geq 1.2 \times 10^8$ $\geq 6 \times 10^7$	$\geq 3 \times 10^7$ $\geq 1 \times 10^7$
Responsivity - Width Product at λ_{op}	$\text{V} \times \text{mm}/\text{W}$	≥ 0.6	≥ 0.1
Response time	ns	≤ 7	≤ 1
Resistance	Ω	15 to 300	10 to 150
Optical area length \times width	mm \times mm	0.25 \times 0.25; 0.5 \times 0.5; 1 \times 1; 2 \times 2	
Operating temperature	K	300	
Acceptance angle, F#	Deg	60, 0.5	

* Data sheet states minimum D^* values for each detector model. Higher performance detectors can be provided upon request. See application notes for more details.



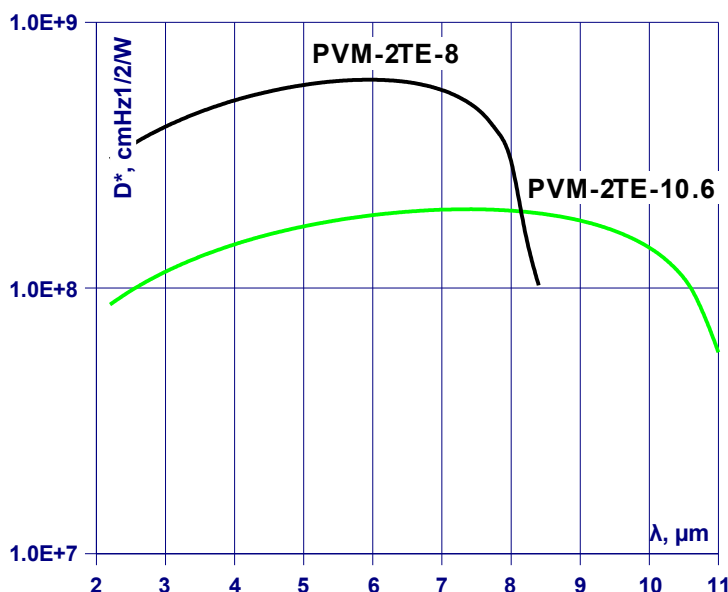
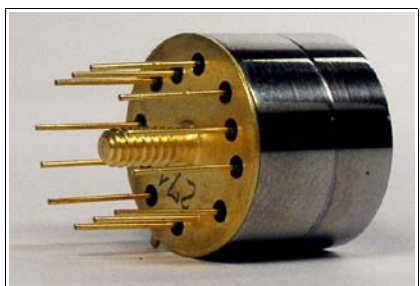
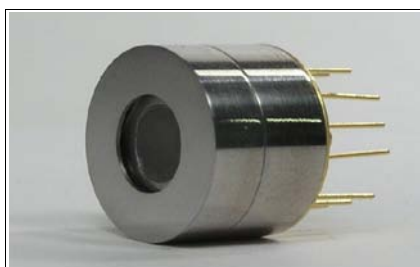
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PVM-2TE-series

2-12 μm IR PHOTOVOLTAIC DETECTORS THERMOELECTRICALLY COOLED



FEATURES

- High performance in the long wavelength range without LN-cooling
- Fast response
- No flicker noise
- Convenient to use
- Wide dynamic range
- Compact, rugged and reliable
- Low cost
- Prompt delivery
- Custom design upon request

DESCRIPTION

The PVM-2TE-n series (where n is wavelength λ_{op} , in micrometers, for which the detector is optimized) photo-detectors are two-stage TE-cooled IR photovoltaic detectors. These devices are optimized for maximum performance at long wavelength with active large area. Standard detectors are available in modified TO-8 packages with BaF₂ windows. High performance and stability are achieved by using a newly optimized variable gap semiconductor (HgCdTe), by optimized composition and doping profiles, and by improved surface processing. Custom devices with quadrant cells, multielement arrays, specialized packages, connectors, windows and optical filters are available on request. See application notes for more details.

SPECIFICATION

@ 20°C

CHARACTERISTICS	UNITS	PVM-2TE-8	PVM-2TE-10.6
λ_{op}	μm	8	10.6
Detectivity:			
at λ_{peak}	cmHz ^{1/2} /W	≥6x10 ⁸	≥2x10 ⁸
at λ_{op}		≥3x10 ⁸	≥1x10 ⁸
Responsivity - Width Product at λ_{op}*	V×mm/W	≥2	≥0.5
Response time	ns	≤7	≤3
Resistance*	Ω	40 to 300	30 to 200
Optical area length × width	mm×mm	0.25×0.25; 0.5×0.5; 1×1; 2×2;	
Operating temperature*	K	220-240	
Acceptance angle, F#*	deg	60, 0.5	

* Data sheet states minimum D* values for each detector model. Higher performance detectors can be provided upon request. See application notes for more details.



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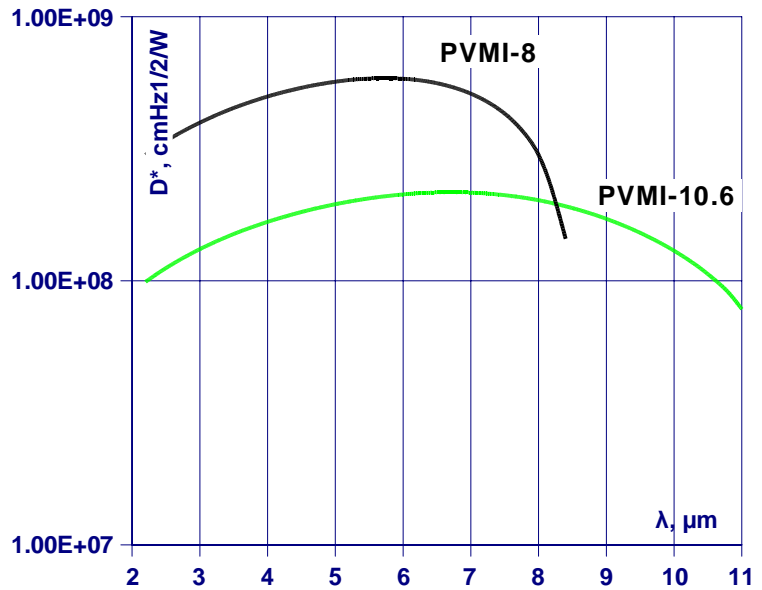
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AP, 05.01.06

SERIES PVMI

2-12 μm IR PHOTOVOLTAIC FAST IR DETECTORS OPTICALLY IMMERSED



FEATURES

- Ambient temperature operation
- No bias required
- Fast response time
- No flicker (1/f) noise
- Operation from DC to VHF
- Perfect match to fast electronics
- Wide dynamic range
- Large area devices
- Low cost
- Custom design upon request

DESCRIPTION

The PVMI-n series photodetectors (where n is wavelength λ_{op} in micrometers, for which the device is optimized) are multiple heterojunction photovoltaic IR detectors which have been optically immersed on high refractive index GaAs hyperhemispherical (standard) or hemispherical (optional) lenses. Optimization is first for maximum sensitivity at λ_{op} then for speed of response. These devices are especially useful as *fast* large area detectors operating within the 2 to 12 μm range. High performance and stability are achieved by using a variable bandgap (Hg,Cd)Te semiconductor, optimized doping, and improved surface processing. Custom quadrant cells, multielement arrays, other immersion lenses, windows and optical filters are available on request. Standard detectors are available in modified TO-39 or BNC-based packages with no windows. Other packages, windows and connectors are available upon request.

SPECIFICATION*

@ 20°C

CHARACTERISTICS	UNITS	PVMI-8	PVMI-10.6
λ_{op}	μm	8	10.6
Detectivity:			
at λ_{peak}	$\text{cmHz}^{1/2}/\text{W}$	$\geq 6 \times 10^8$	$\geq 2 \times 10^8$
at λ_{op}		$\geq 3 \times 10^8$	$\geq 1 \times 10^8$
Responsivity - Width Product at λ_{op}	$\text{V} \times \text{mm}/\text{W}$	≥ 3	≥ 0.5
Response time	ns	≤ 7	≤ 1
Resistance	ohms	15-300	10-150
Optical area length x width	mm x mm	0.25x0.25; 0.5x0.5; 1x1; 2x2;	
Operating temperature	K	300	
Acceptance angle, F#	deg	35, 1.65	

- Data sheet states minimum D^* values for each detector model. Higher performance detectors can be provided upon request. See application notes for more details.



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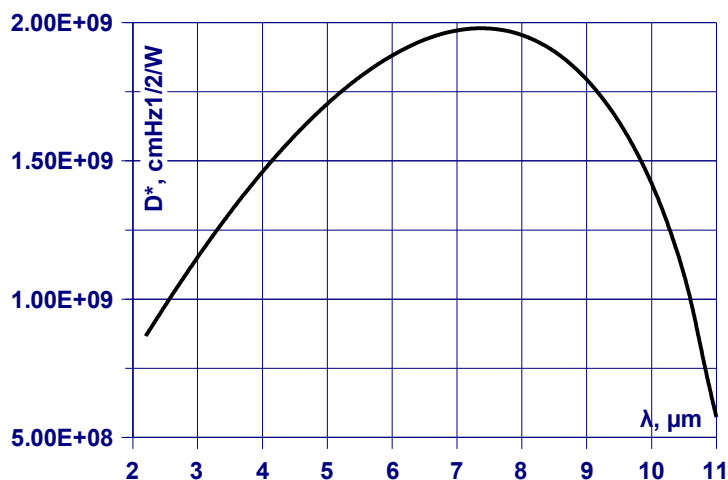
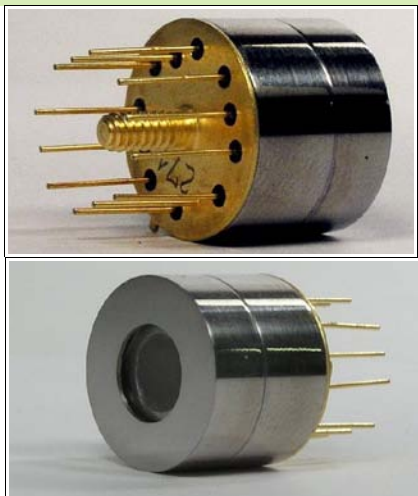
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SERIES PVMI-2TE

8-12 μm IR PHOTOVOLTAIC MULTIPLE JUNCTION DETECTORS

THERMOELECTRICALLY COOLED

OPTICALLY IMMERSED



● FEATURES

- High performance in the long wavelength range without LN-cooling
- Fast response
- No flicker noise
- Convenient to use
- Wide dynamic range
- Compact, rugged and reliable
- Low cost
- Prompt delivery
- Custom design upon request

● DESCRIPTION



The PVMI-2TE-10.6 (where 10.6 is wavelength λ_{op} in micrometers, at which the detector is optimized) is a two-stage TE-cooled IR photovoltaic detector which is been optically immersed on a high refractive index GaAs hemispherical or hyperhemispherical lens. These devices are our maximum performance long wavelength large area devices. High performance and stability are achieved by using a newly developed variable bandgap semiconductors (HgCdTe) with optimized composition and doping profiles and with improved surface processing. Standard detectors are available in modified TO-8 packages with BaF₂ windows. Other packages and windows are available upon request. See application notes for more details. Custom devices with quadrant cells, multielement arrays, specialized packages, connectors, windows and optical filters are available on request.

SPECIFICATION

@ 20°C

CHARACTERISTICS	UNITS	PVMI-2TE-10.6
λ_{op}	μm	10.6
Detectivity:		
at λ_{peak}	$\text{cmHz}^{1/2}/\text{W}$	$\geq 2 \times 10^9$
at λ_{op}		$\geq 1 \times 10^9$
Responsivity - Width Product at λ_{op}	$\text{V} \times \text{mm} / \text{W}$	≥ 7
Response time	ns	≤ 3
Resistance*	Ω	30÷200
Optical area length × width	mm×mm	0.1×0.1; 0.25×0.25; 0.5×0.5; 1×1; 2×2;
Operating temperature*	K	220÷240
Acceptance angle, F#*	deg	35, 1.65

* Data sheet states minimum D^* values for each detector model. Higher performance detectors can be provided upon request. See application notes for more details.

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